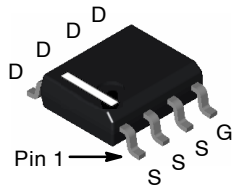
MOSFET – P-Channel, Shielded Gate, POWERTRENCH®

-150 V, -2.2 A, 255 mΩ

FDS86267P

V_{DS}	$R_{DS(on)}$ MAX	I_D MAX
−150 V	255 mΩ @ −10 V	−2.2 A
	290 mΩ @ −6 V	



SOIC8
CASE 751EB

General Description

This P−Channel MOSFET is produced using **onsemi**'s advanced POWERTRENCH process that incorporates shielded gate technology. The process has been optimized for the on−state resistance and yet maintain superior switching performance.

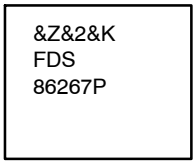
Features

- Shielded Gate MOSFET Technology
- Max $R_{DS(ON)}$ = 255 mΩ @ V_{GS} = −10 V, I_D = −2.2 A
- Max $R_{DS(ON)}$ = 290 mΩ @ V_{GS} = −6 V, I_D = −2 A
- Very Low $R_{DS(on)}$ Mid Voltage P−channel Silicon Technology Optimised for Low Qg
- This Product is Optimised for Fast Switching Applications as well as Load Switch Applications
- 100% UIL Tested
- This Device is Pb−Free, Halide Free and is RoHS Compliant

Applications

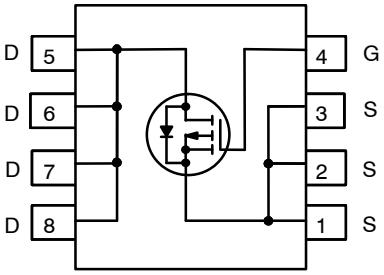
- Active Clamp Switch
- Load Switch

MARKING DIAGRAM



&Z	= Assembly Plant Code
&2	= 2−Digit Date Code (Year & Week)
&K	= 2−Digit Lot Run Traceability Code
FDS86267P	= Specific Device Code

PIN CONNECTIONS



ORDERING INFORMATION

Device	Package	Shipping†
FDS86267P	SOIC8	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

© Semiconductor Components Industries, LLC, 2015

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Parameter		Ratings	Unit
V_{DS}	Drain to Source Voltage		−150	V
V_{GS}	Gate to Source Voltage		±25	V
I_D	Drain Current	Continuous (Note 1a)	−2.2	A
		Pulsed (Note 4)	−34	
E_{AS}	Single Pulse Avalanche Energy (Note 3)		54	mJ
P_D	Power Dissipation	T_A = 25°C (Note 1a)	2.5	W
		T_A = 25°C (Note 1b)	1.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	°C/W
	Thermal Resistance, Junction to Ambient (Note 1b)	125	

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = −250 μA, V_{GS} = 0 V	−150	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = −250 μA, Referenced to 25°C	–	−121	–	mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = −120 V, V_{GS} = 0 V	–	–	−1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±25 V, V_{DS} = 0 V	–	–	±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = −250 μA	−2	−3	−4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = −250 μA, Referenced to 25°C	–	5	–	mV/°C
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = −10 V, I_D = −2.2 A	–	191	255	mΩ
		V_{GS} = −6 V, I_D = −2 A	–	214	290	
		V_{GS} = −10 V, I_D = −2.2 A, T_J = 125°C	–	342	448	
g_{FS}	Forward Transconductance	V_{DS} = −10 V, I_D = −2.2 A	–	6.8	–	S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = −75 V, V_{GS} = 0 V, f = 1 MHz	–	806	1130	pF
C_{oss}	Output Capacitance		–	54	75	pF
C_{rss}	Reverse Transfer Capacitance		–	1.6	2.3	pF
R_g	Gate Resistance		0.1	3	6	Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = −75 V, I_D = −2.2 A, V_{GS} = −10 V, R_{GEN} = 6 Ω	–	9.7	20	ns
t_r	Rise Time		–	2.5	10	ns
$t_{d(off)}$	Turn–Off Delay Time		–	17	30	ns
t_f	Fall Time		–	5.7	12	ns

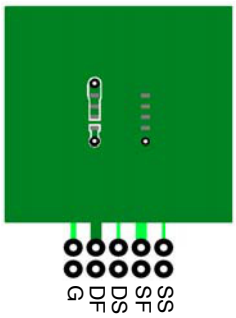
Share Feedback
Your Opinion Matters

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (continued)

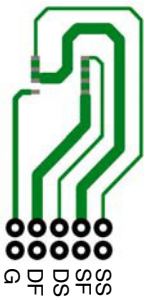
Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS						
Q_g	Total Gate Charge	V_{GS} = 0 V to −10 V, V_{DD} = −75 V, I_D = −2.2 A	–	11	16	nC
		V_{GS} = 0 V to −6 V, V_{DD} = −75 V, I_D = −2.2 A	–	7	10	nC
Q_{gs}	Gate to Source Charge	V_{DD} = −75 V, I_D = −2.2 A	–	3.2	–	nC
Q_{gd}	Gate to Drain “Miller” Charge		–	1.9	–	nC
DRAIN−SOURCE DIODE CHARACTERISTICS						
V_{SD}	Source−Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = −2.2 A (Note 2)	–	−0.8	−1.3	V
		V_{GS} = 0 V, I_S = −2 A (Note 2)	–	−0.8	−1.2	
t_{rr}	Reverse Recovery Time	I_F = −2.2 A, di/dt = 100 A/μs	–	65	104	ns
Q_{rr}	Reverse Recovery Charge		–	157	251	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR−4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user’s board design.



a. 50°C/W when mounted on a 1 in^2 pad of 2 oz copper.



b. 125°C/W when mounted on a minimum pad.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0 %.
3. Starting T_J = 25°C, L = 3 mH, I_{AS} = −6 A, V_{DD} = −150 V, V_{GS} = −10 V. 100% tested at L = 0.3 mH, I_{AS} = −13 A.
4. Pulsed Id please refer to Figure 11 SOA graph for more details.

Share Feedback
Your Opinion Matters

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

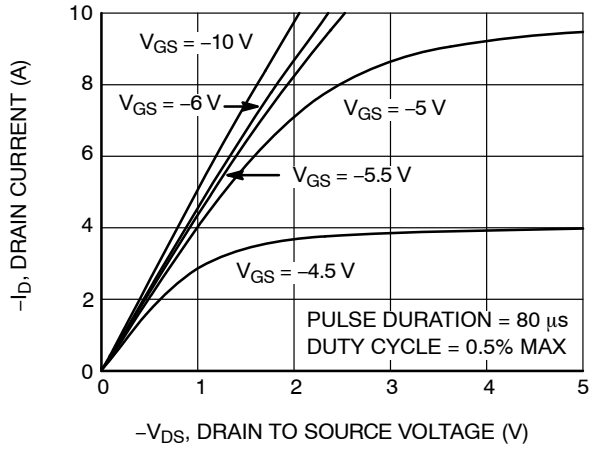


Figure 1. On Region Characteristics

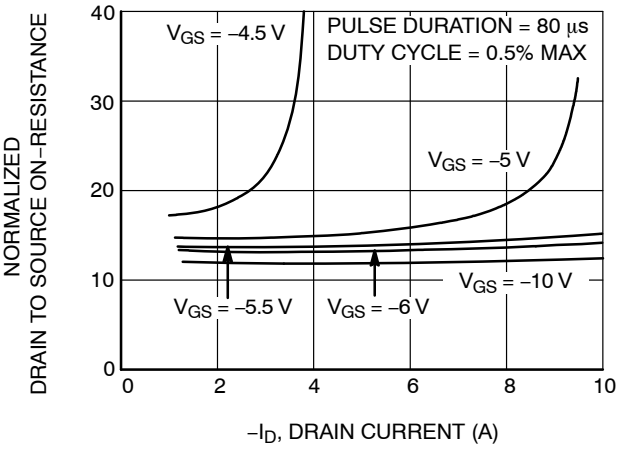


Figure 2. Normalized On−Resistance vs. Drain Current and Gate Voltage

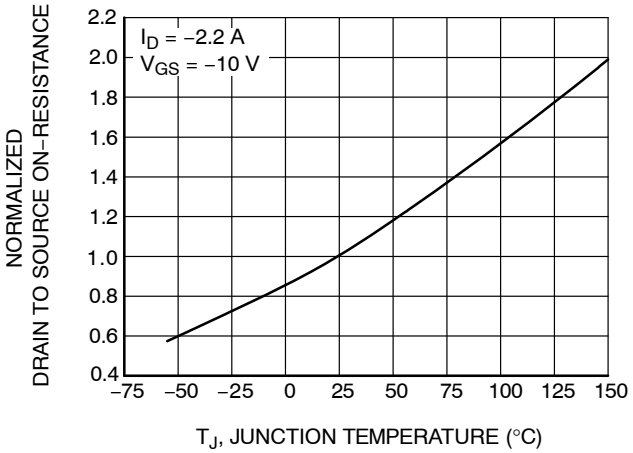


Figure 3. Normalized On Resistance vs. Junction Temperature

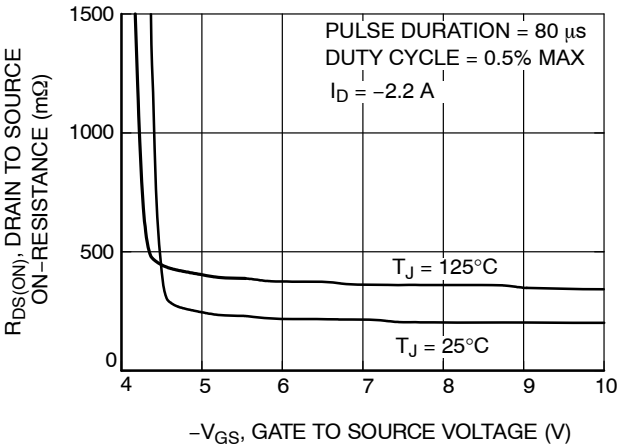


Figure 4. On−Resistance vs. Gate to Source Voltage

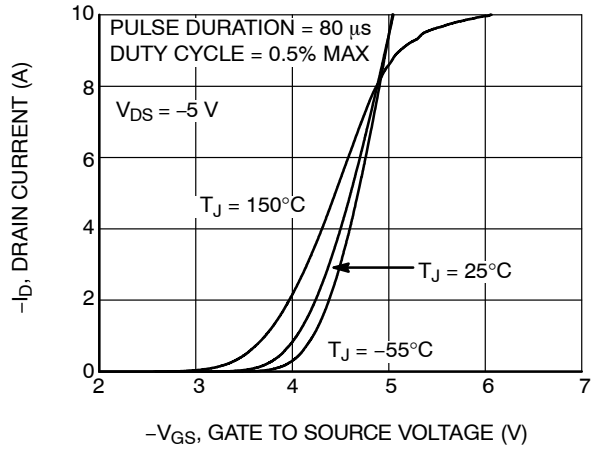


Figure 5. Transfer Characteristics

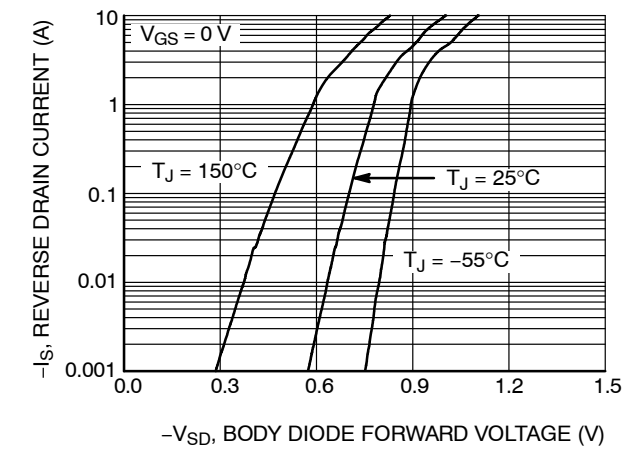


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Share Feedback
Your Opinion Matters

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (continued)

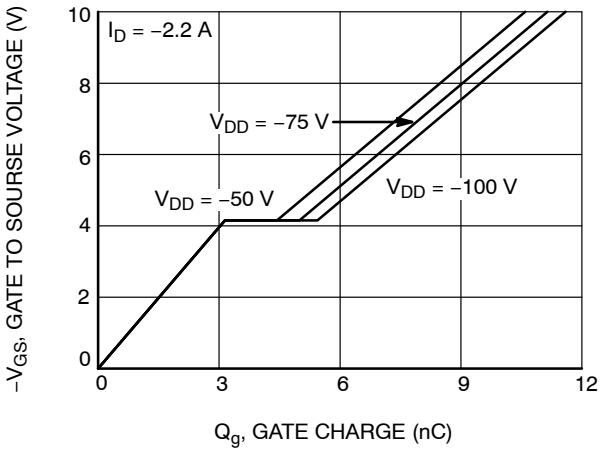


Figure 7. Gate Charge Characteristics

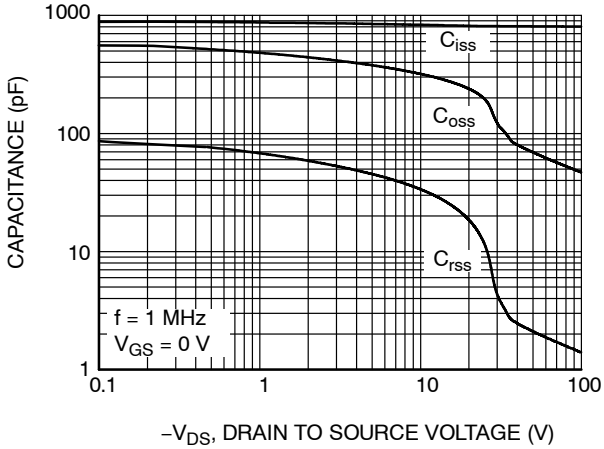


Figure 8. Capacitance vs. Drain to Source Voltage

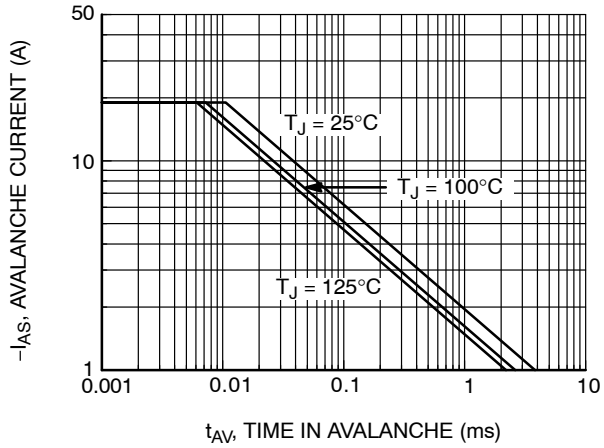


Figure 9. Unclamped Inductive Switching Capability

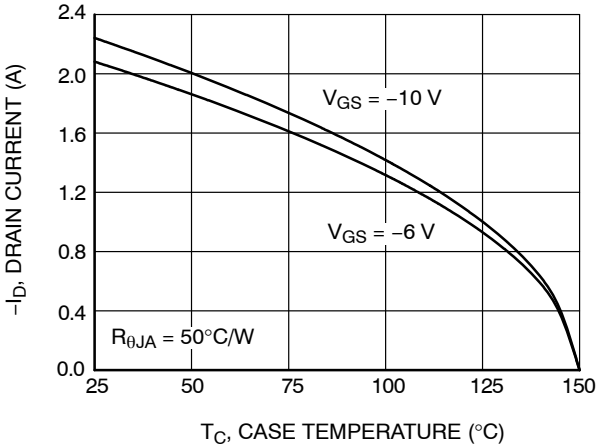


Figure 10. Maximum Continuous Drain Current vs. Ambient Temperature

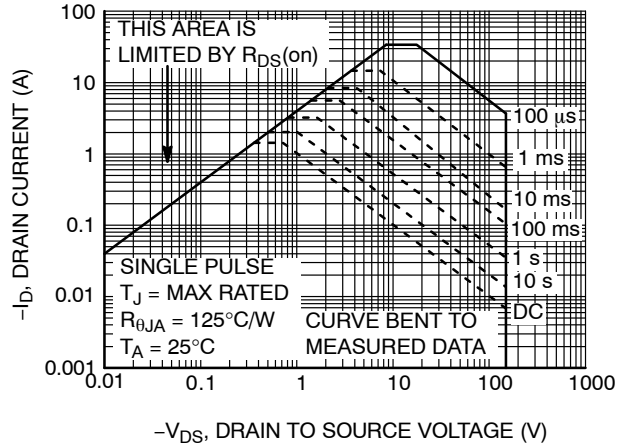


Figure 11. Forward Bias Safe Operating Area

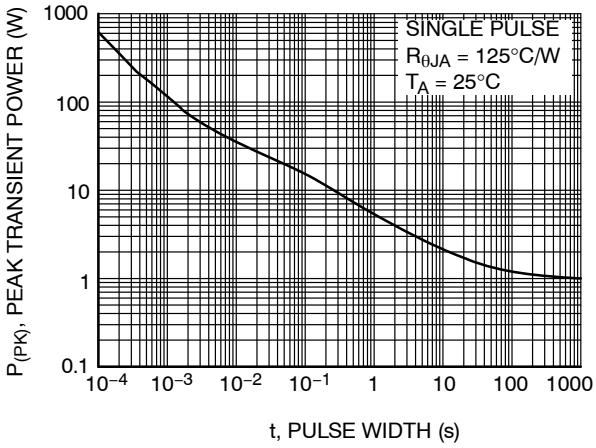


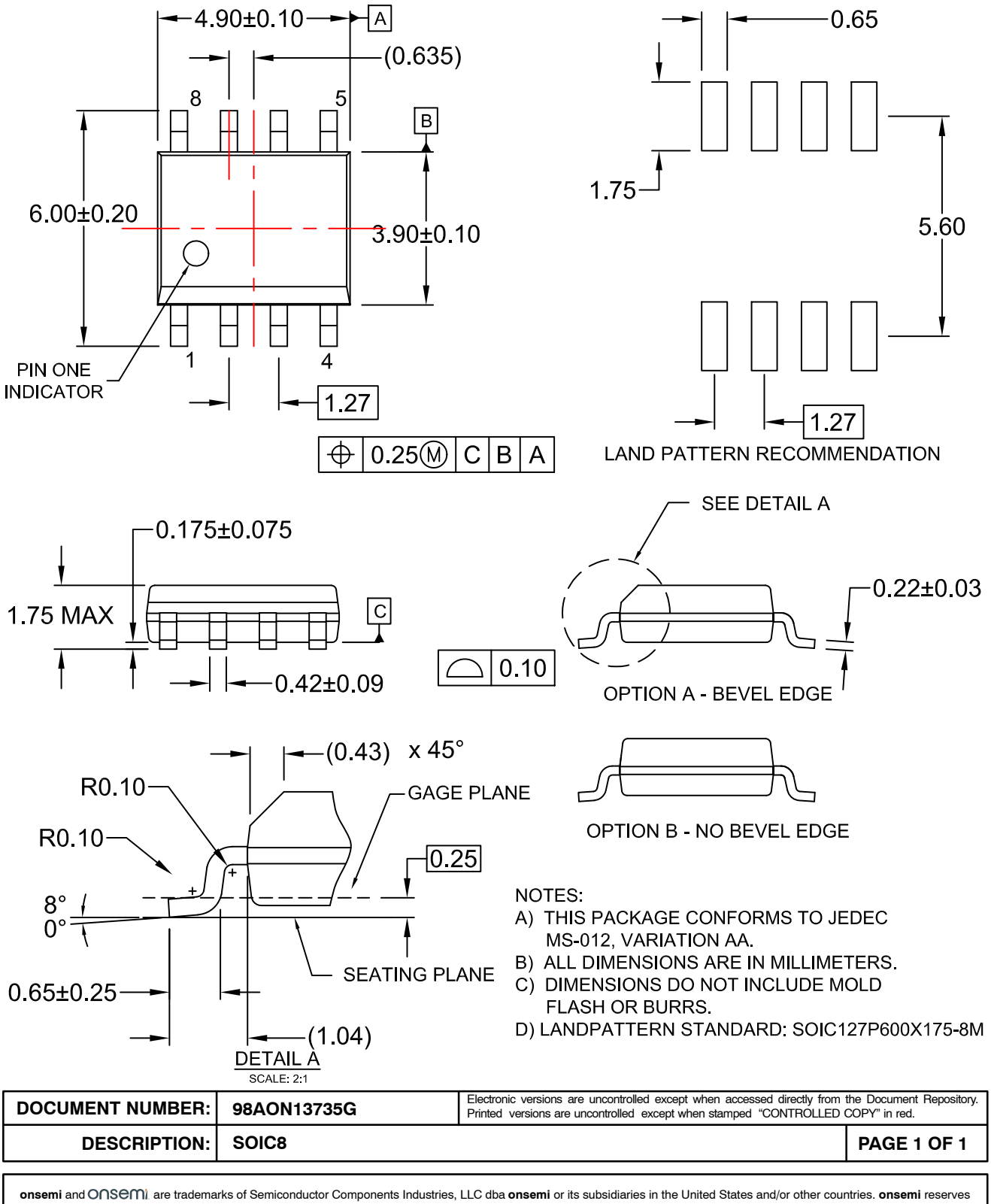
Figure 12. Single Pulse Maximum Power Dissipation

POWERTRENCH is a registered trademark of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries.

Share Feedback
Your Opinion Matters

SOIC8
CASE 751EB
ISSUE A

DATE 24 AUG 2017



NOTES:
A) THIS PACKAGE CONFORMS TO JEDEC MS-012, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
D) LANDPATTERN STANDARD: SOIC127P600X175-8M

DOCUMENT NUMBER:	**98AON13735G**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**SOIC8**	**PAGE 1 OF 1**

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

onsemi, , and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

ENTEGRECİ

Bu belge www.entegreci.com üzerinden sunulmaktadır.

Elektronik komponent tedarikinde Entegreci

Entegreci, Eskişehir merkezli, Türkiye geneline satış yapan bir elektronik komponent mağazasıdır. Entegreler (IC), mikrodenetleyiciler, transistörler, diyotlar, pasif elemanlar, konnektörler, modüller ve geliştirme kartları tek adetten seri üretim adetlerine kadar satılır. Ürün sayfalarında güncel stok durumunu, fiyatı ve datasheet bağlantısını bulabilirsiniz.

Parça koduyla arama

Üretici parça numarasını yazın; stok ve fiyatı hemen görün.

www.entegreci.com

Ürün kategorileri

Entegreden kapasitöre tüm elektronik komponent kategorileri.

Kategorilere göz atın

Üreticiler

Aradığınız üreticinin ürünlerini tek sayfada inceleyin.

Üreticileri görün

Toplu alım ve teklif

Listede olmayan ya da yüksek adetli parçalar için teklif isteyin.

Teklif isteyin

www.entegreci.com | **destek@entegreci.com** | **0850 305 90 34**

Entegreci is an online electronic components store based in Türkiye. Search by manufacturer part number to see stock, prices and datasheets for integrated circuits, microcontrollers, transistors, passive components and connectors, or request a quote for parts that are not listed.

Bu sayfa Entegreci tarafından eklenmiştir. Belgenin önceki sayfaları asıl yayıncısına aittir ve içeriği değiştirilmemiştir; en güncel sürüm için belgenin yayıncısına başvurun.